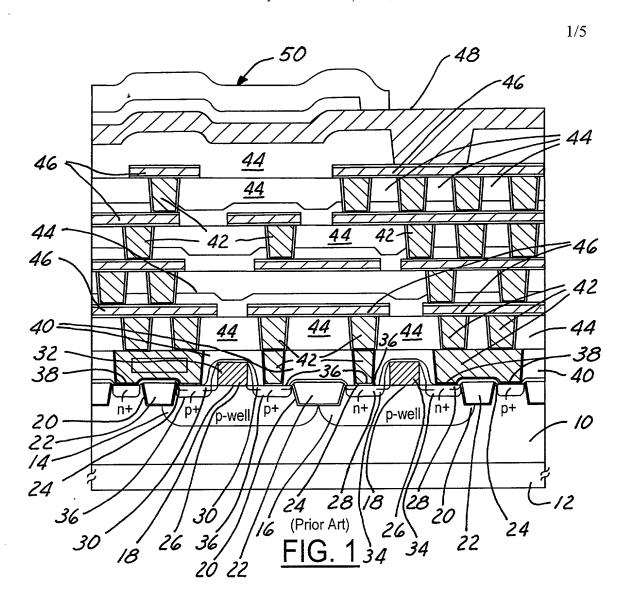
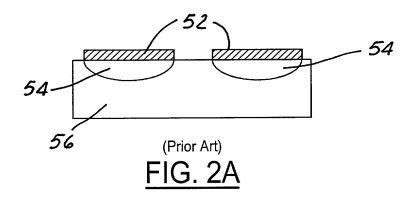
Inventor(s): Lai, et al Serial No.: To Be Assigned Filed: Herewith

For: Method Of Wet Etching Low Dielectric Constant Materials

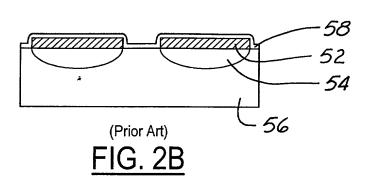
Attorney Docket No.: 67,200-473

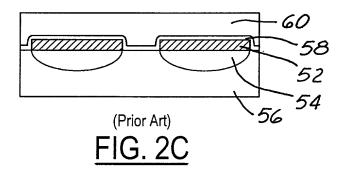




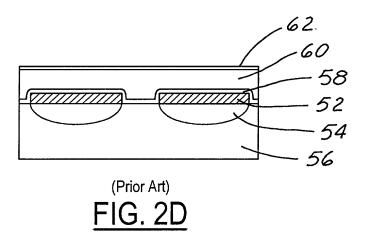
For: Method Of Wet Etching Low Dielectric Constant Materials

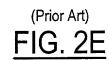
Attorney Docket No.: 67,200-473

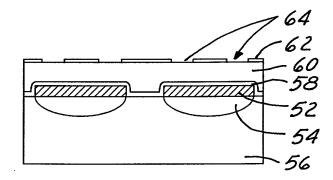




2/5



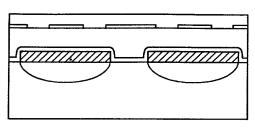




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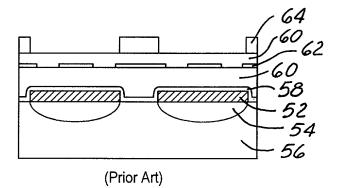
For: Method Of Wet Etching Low Dielectric Constant Materials

Attorney Docket No.: 67,200-473



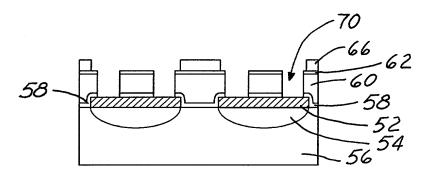
(Prior Art)

FIG. 2F



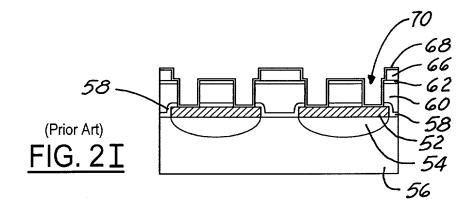
3/5

FIG. 2G



(Prior Art)

FIG. 2H



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For: Method Of Wet Etching Low Dielectric Constant Materials

Attorney Docket No.: 67,200-473

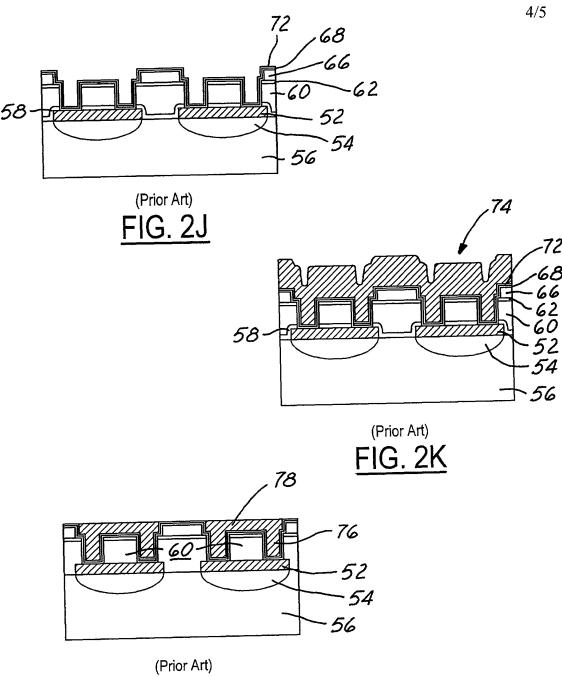
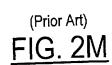
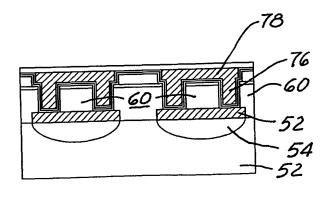


FIG. 2L



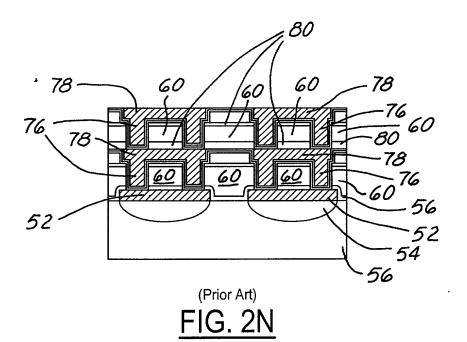


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Attorney Docket No.: 67,200-473

5/5



Providing or Forming a Semiconductor Device having Two Metal Interconnects and a Low Dielectric Constant Material There Between

Etching the Low Dieletric Constant Material with an Aqueous Solution Including HF and HCL

Analyzing the Etched Device with a Scanning Electron Microscope

FIG. 3